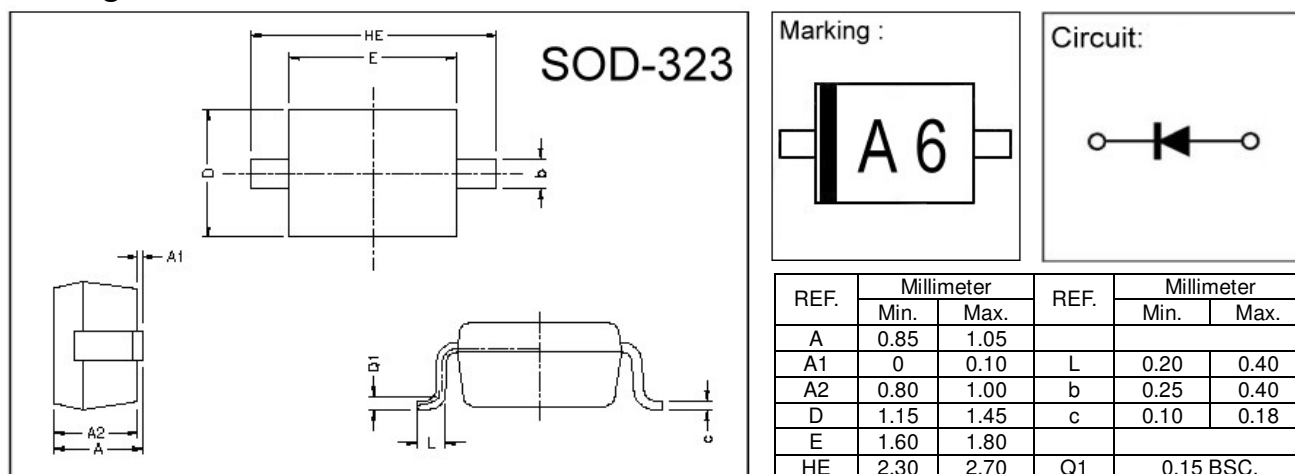


GDBAS16**SURFACE MOUNT, SWITCHING DIODE**
VOLTAGE 85V, CURRENT 250mA**Description**

The GDBAS16 is designed for high-speed switching application in hybrid thick and thin-film circuits. The devices is manufactured by the silicon epitaxial planar process and packed in a plastic surface mount package.

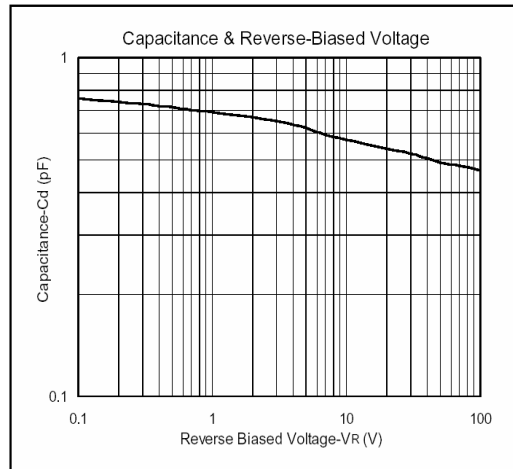
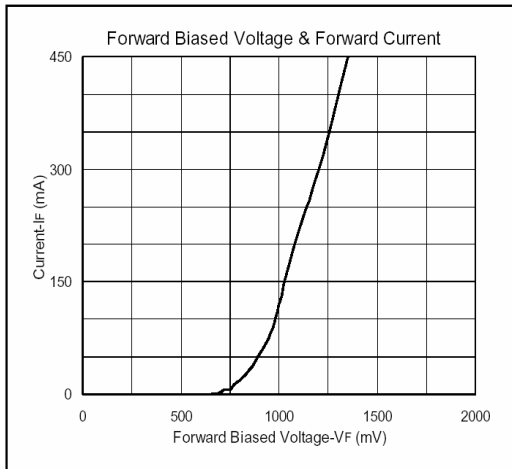
Package Dimensions**Absolute Maximum Ratings at TA = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-65 ~ +150	°C
Reverse Voltage	V _R	85	V
Repetitive Reverse Voltage	V _{RRM}	85	V
Forward Current	I _O	250	mA
Repetitive Forward Current	I _{FM}	500	mA
Forward Surge Current (1ms)	I _{FSM}	1000	mA
Total Power Dissipation	P _D	225	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V _(BR)	85	-	V	I _R =100uA
Forward Voltage	V _{F(1)}	-	715	mV	I _F =1mA
	V _{F(2)}	-	855	mV	I _F =10mA
	V _{F(3)}	-	1000	mV	I _F =50mA
	V _{F(4)}	-	1250	mV	I _F =150mA
Reverse Current	I _R	-	1	uA	V _R =85V
Total Capacitance	C _T		2	pF	V _R =0, f=1MHz
Reverse Recovery Time	T _{rr}	-	6	nS	I _F =I _R =10mA, R _L =100Ω measured at I _R =1mA

Characteristics Curve

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